

L Number	Hits	Search Text	DB	Time stamp
1	9	gate\$1 near2 length\$1 with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:25
8	0	("L.sub.g") with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:29
15	1	("G.sub.1") with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:30
22	85	((scan\$4 and data) near2 (line\$1)) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:03
29	5	KAWATA-HIROTAKA	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:49
57	642	(257/72).CCLS.	USPAT	2002/10/22 15:54
58	5	(monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18
65	0	monocrystalline adj silicon with semiconductor adj layer with preferably	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:57
72	1	monocrystalline adj silicon with semiconductor adj layer with prefer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:58
79	1	monocrystalline adj silicon with semiconductor adj layer\$1 with prefer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18
86	139	single adj crystalline adj silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18
93	396	(monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:01
100	3	(single adj crystalline adj silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:19
107	9	((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20

114	1	((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) not ((single adj crystalline adj silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20
121	4	mono adj crystalline near2 silicon with semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20
50	186	monocrystalline adj silicon with semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:48
128	33977	(monocrystalline adj silicon with semiconductor adj layer) and tft thin adj film adj transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:50
135	33	(monocrystalline adj silicon with semiconductor adj layer) and (tft thin adj film adj transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:50
142	1056	(monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:58
149	7	((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) not ((single adj crystalline adj silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
156	47	(monocrystal\$4) near2 silicon with semiconductor adj film\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
163	630	156and ((257/72).CCLS.) not ((single adj crystalline adj silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.) ) ((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1 ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59

170	0	((monocrystal\$4) near2 silicon with semiconductor adj film\$1) and ((257/72).CCLS.) not (((single adj crystalline adj silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1 ) and ((257/72).CCLS.) ) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.) ) ((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1 ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
177	6	(monocrystal\$4) near2 (Si "si") with semiconductor adj film\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:00
184	293	(monocrystal\$4) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:01
191	51	(monocrystal\$4) near2 silicon with semiconductor adj layer\$1 and (tft\$1 thin adj film adj transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:02